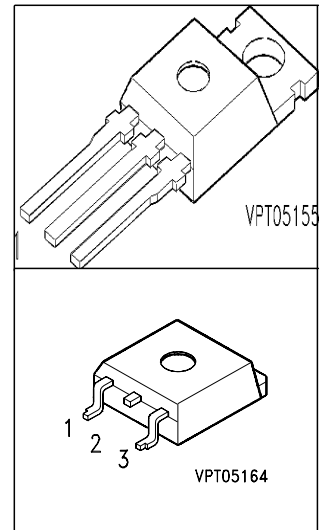
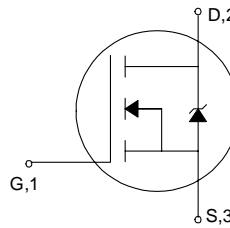


Cool MOS™ Power-Transistor

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Optimized capacitances
- Improved noise immunity
- Former development designation:
SPPx3N60S5/SPBx3N60S5



Type	V_{DS}	I_D	$R_{DS(on)}$	Package	Marking	Ordering Code
SPP07N60S5	600 V	7.3 A	0.6 Ω	P-TO220-3-1	07N60S5	Q67040-S4172
SPB07N60S5				P-TO263-3-2	07N60S5	Q67040-S4185

Maximum Ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ }^\circ\text{C}$ $T_C = 100\text{ }^\circ\text{C}$	I_D	7.3 4.6	A
Pulsed drain current, $t_p = 1\text{ ms}^1)$ $T_C = 25\text{ }^\circ\text{C}$	$I_{D\text{ puls}}$	14.6	
Avalanche energy, single pulse $I_D = 7.3\text{ A}$, $V_{DD} = 50\text{ V}$	E_{AS}	230	mJ
Avalanche energy (repetitive, limited by T_{jmax}) $I_D = 9.1\text{ A}$, $V_{DD} = 50\text{ V}$	E_{AR}	0.8	
Avalanche current (repetitive, limited by T_{jmax})	I_{AR}	9.1	A
Reverse diode dv/dt $I_S = 7.3\text{ A}$, $V_{DS} < V_{DSS}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_{jmax} = 150\text{ }^\circ\text{C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_C = 25\text{ }^\circ\text{C}$	P_{tot}	83	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	-	-	1.5	K/W
Thermal resistance, junction - ambient (Leaded and through-hole packages)	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ²⁾	R_{thJA}	-	-	62	
		-	35	-	

Static Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Drain-source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$	$V_{(BR)DSS}$	600	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 350\text{ }\mu\text{A}$, $T_j = 25\text{ °C}$	$V_{GS(th)}$	3.5	4.5	5.5	
Zero gate voltage drain current, $V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$, $T_j = 25\text{ °C}$ $V_{GS} = 0\text{ V}$, $T_j = 150\text{ °C}$	I_{DSS}	-	0.5	1	μA
		-	-	100	
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	-	100	nA
Drain-source on-state resistance $V_{GS} = 10\text{ V}$, $I_D = 4.6\text{ A}$	$R_{DS(on)}$	-	0.54	0.6	Ω

¹current limited by T_{jmax}
² Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 4.6A$	-	4	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = 25V$, $f = 1MHz$	-	970	-	pF
Output capacitance	C_{oss}		-	370	-	
Reverse transfer capacitance	C_{rss}		-	10	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 350V$, $V_{GS} = 10V$, $I_D = 7.3A$, $R_G = 12\Omega$	-	120	-	ns
Rise time	t_r		-	40	-	
Turn-off delay time	$t_{d(off)}$		-	170	255	
Fall time	t_f		-	20	30	

Gate Charge Characteristics

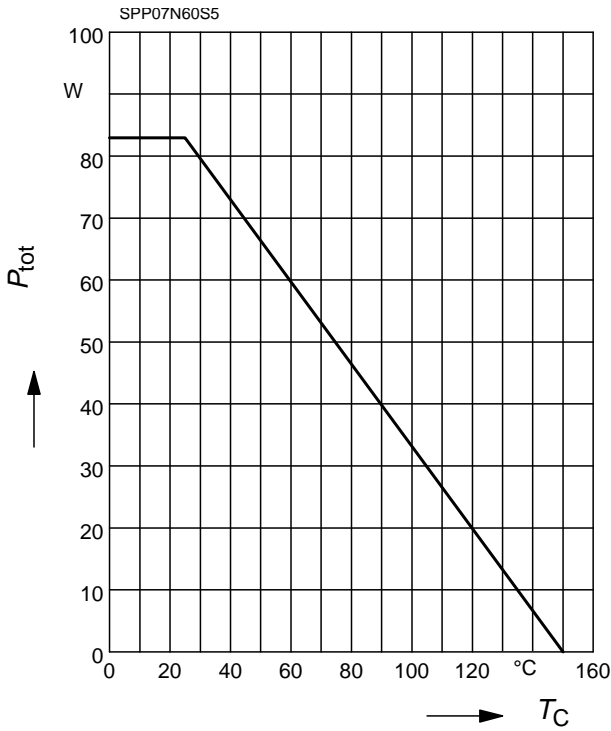
Gate to source charge	Q_{gs}	$V_{DD} = 350V$, $I_D = 7.3A$	-	7.5	-	nC
Gate to drain charge	Q_{gd}		-	16.5	-	
Total gate charge	Q_g	$V_{DD} = 350V$, $I_D = 7.3A$, $V_{GS} = 0$ to $10V$	-	27	35	

Reverse Diode

Inverse diode continuous forward current	I_S	$T_C = 25\text{ °C}$	-	-	7.3	A
Inverse diode direct current, pulsed	I_{SM}		-	-	14.6	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0V$, $I_F = 7.3A$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R = 350V$, $I_F = I_S$, $di_F/dt = 100A/\mu s$	-	750	1275	ns
Reverse recovery charge	Q_{rr}		-	4.9	-	

Power dissipation

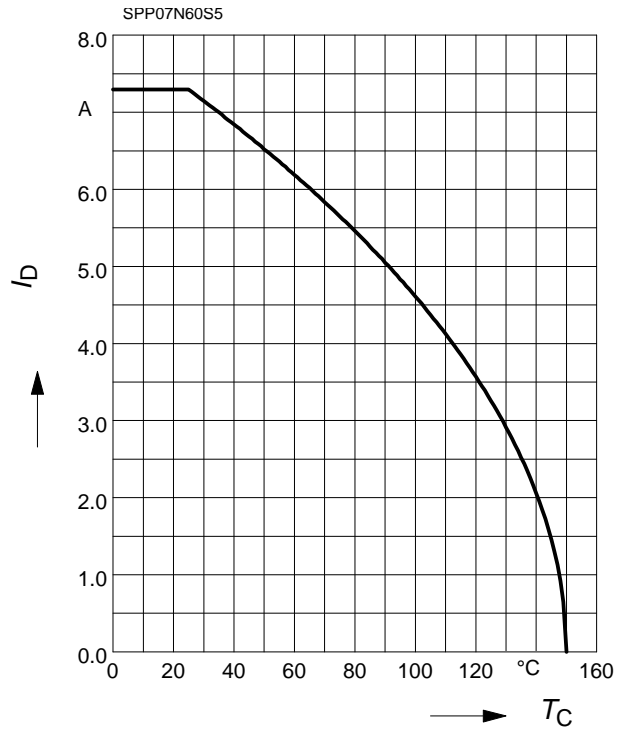
$P_{tot} = f(T_C)$



Drain current

$I_D = f(T_C)$

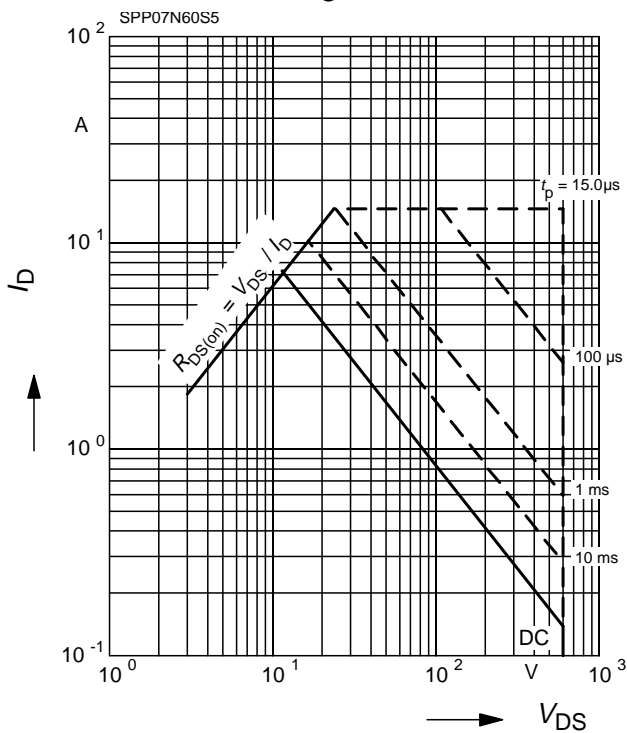
parameter: $V_{GS} \geq 10\text{ V}$



Safe operating area

$I_D = f(V_{DS})$

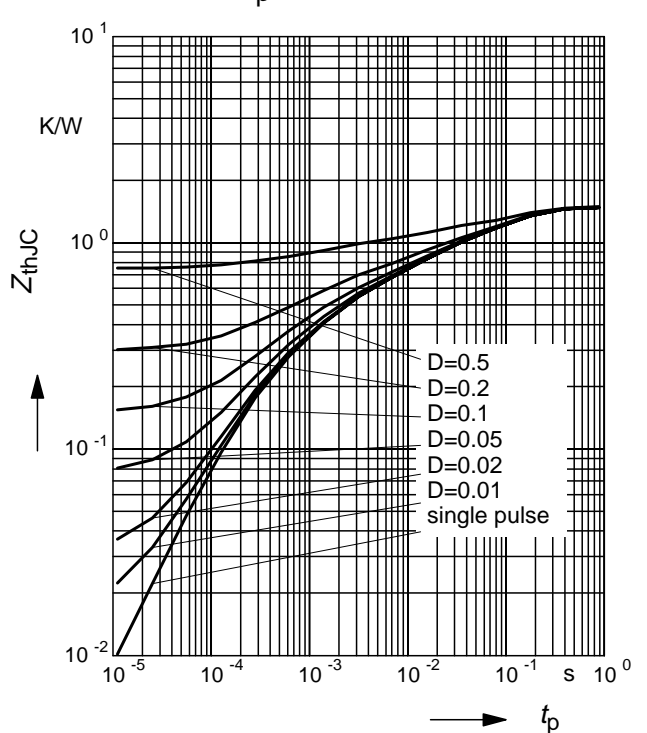
parameter: $D=0.01, T_C=25^\circ\text{C}$



Transient thermal impedance

$Z_{thJC} = f(t_p)$

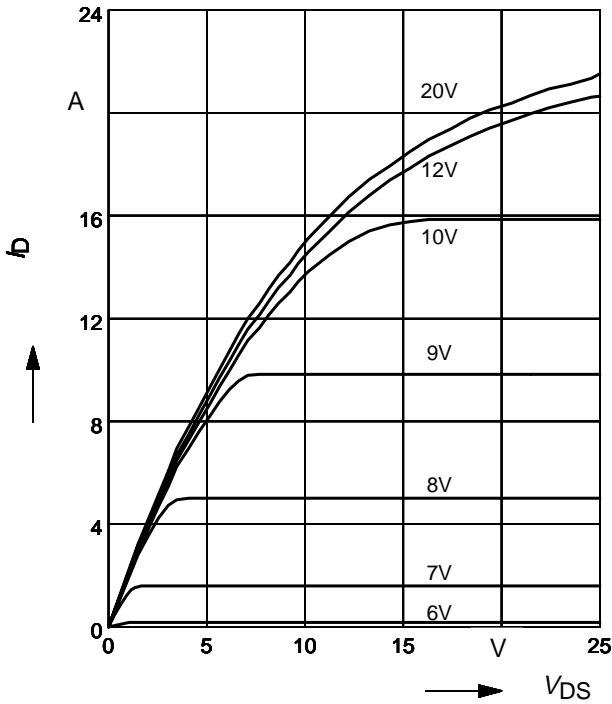
parameter: $D = t_p/T$



Typ. output characteristic

$I_D = f(V_{DS})$

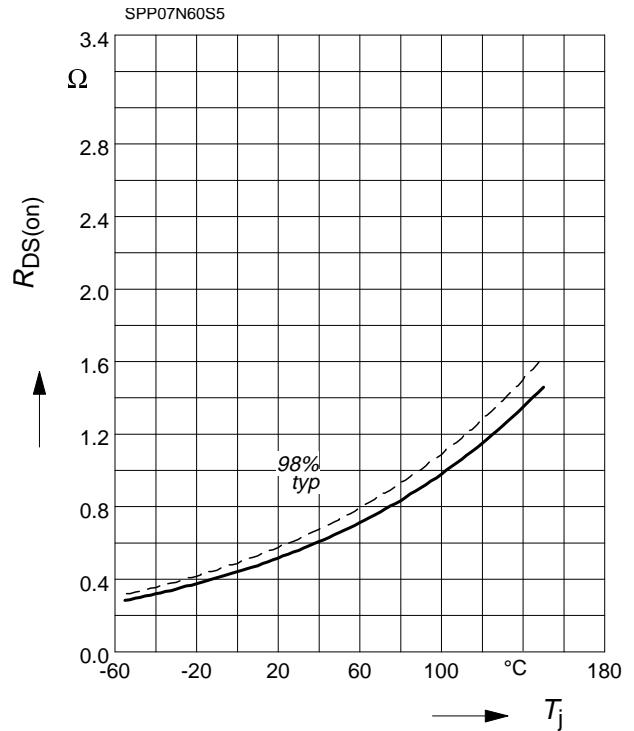
Parameter: $V_{GS}, T_j = 25\text{ }^\circ\text{C}$



Drain-source on-resistance

$R_{DS(on)} = f(T_j)$

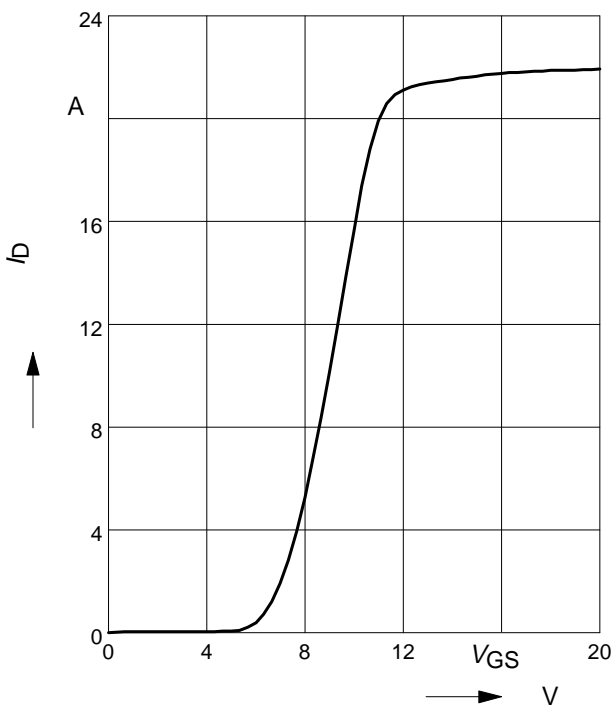
parameter : $I_D = 4.6\text{ A}, V_{GS} = 10\text{ V}$



Typ. transfer characteristics

$I_D = f(V_{GS})$

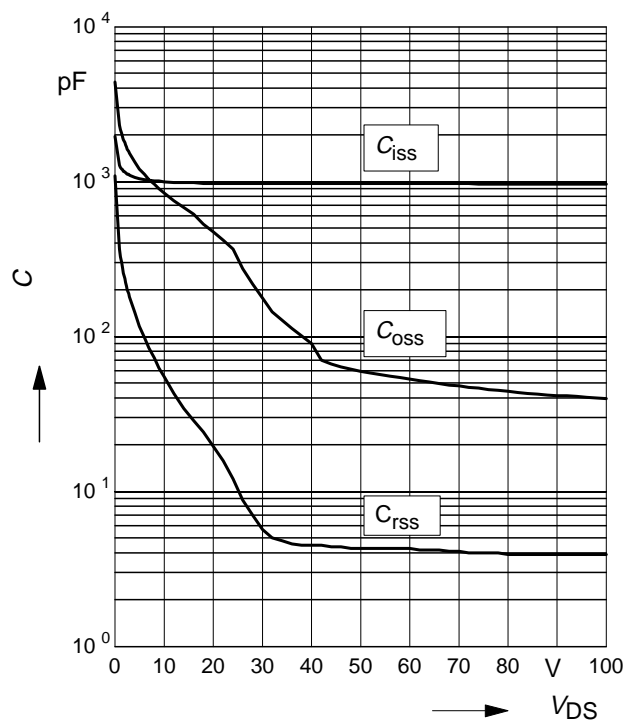
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



Typ. capacitances

$C = f(V_{DS})$

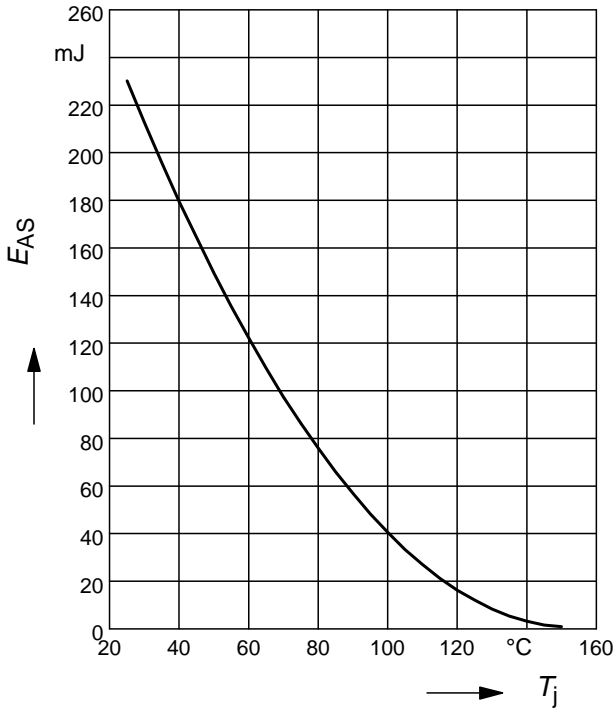
parameter: $V_{GS} = 0\text{ V}, f = 1\text{ MHz}$



Avalanche energy

$$E_{AS} = f(T_j)$$

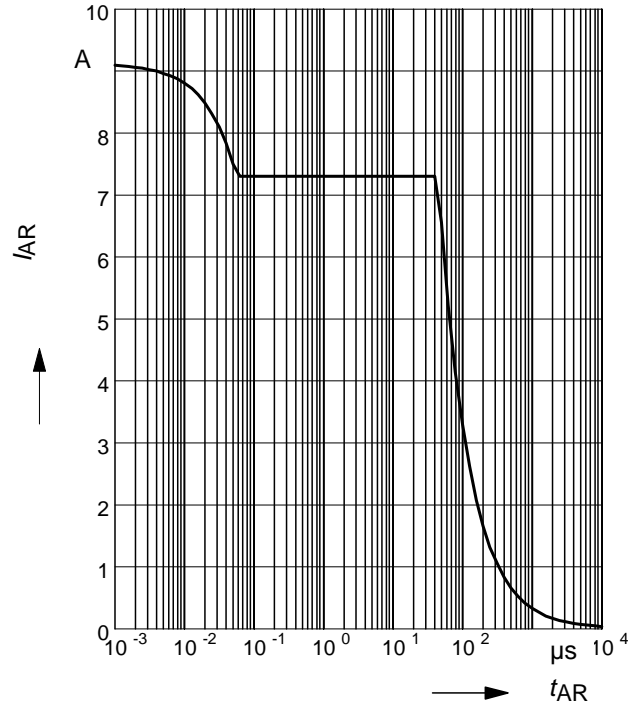
par.: $I_D=7.3A$, $V_{DD}=50V$



Avalanche SOA

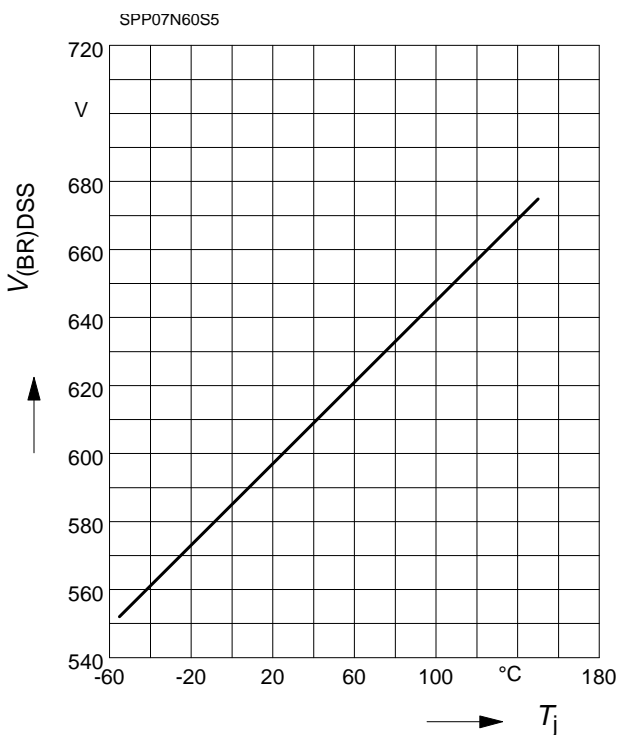
$$I_{AR} = f(t_{AR})$$

par.: $T_{j(START)} = 25\text{ °C}$, $T_j \leq 150\text{ °C}$



Drain-source breakdown voltage

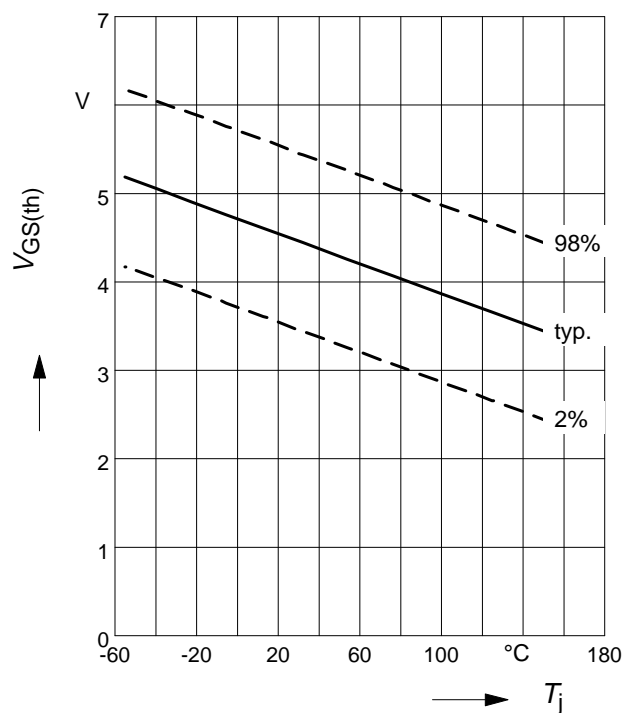
$$V_{(BR)DSS} = f(T_j)$$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

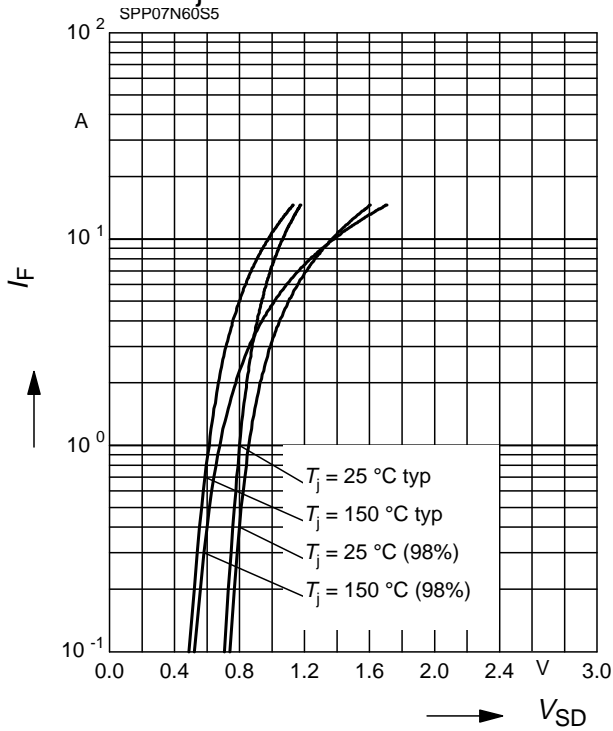
parameter: $V_{GS} = V_{DS}$, $I_D = 350\text{ μA}$



Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

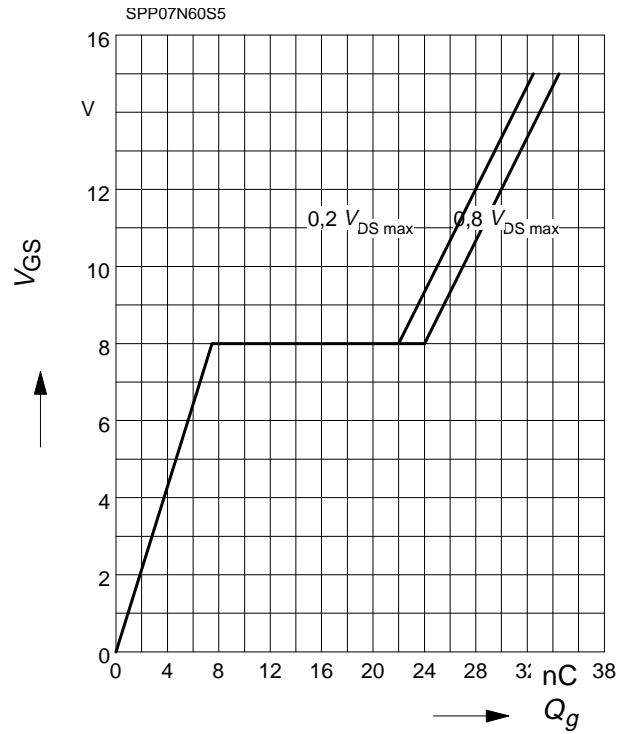
parameter: T_j , $t_p = 80 \mu s$

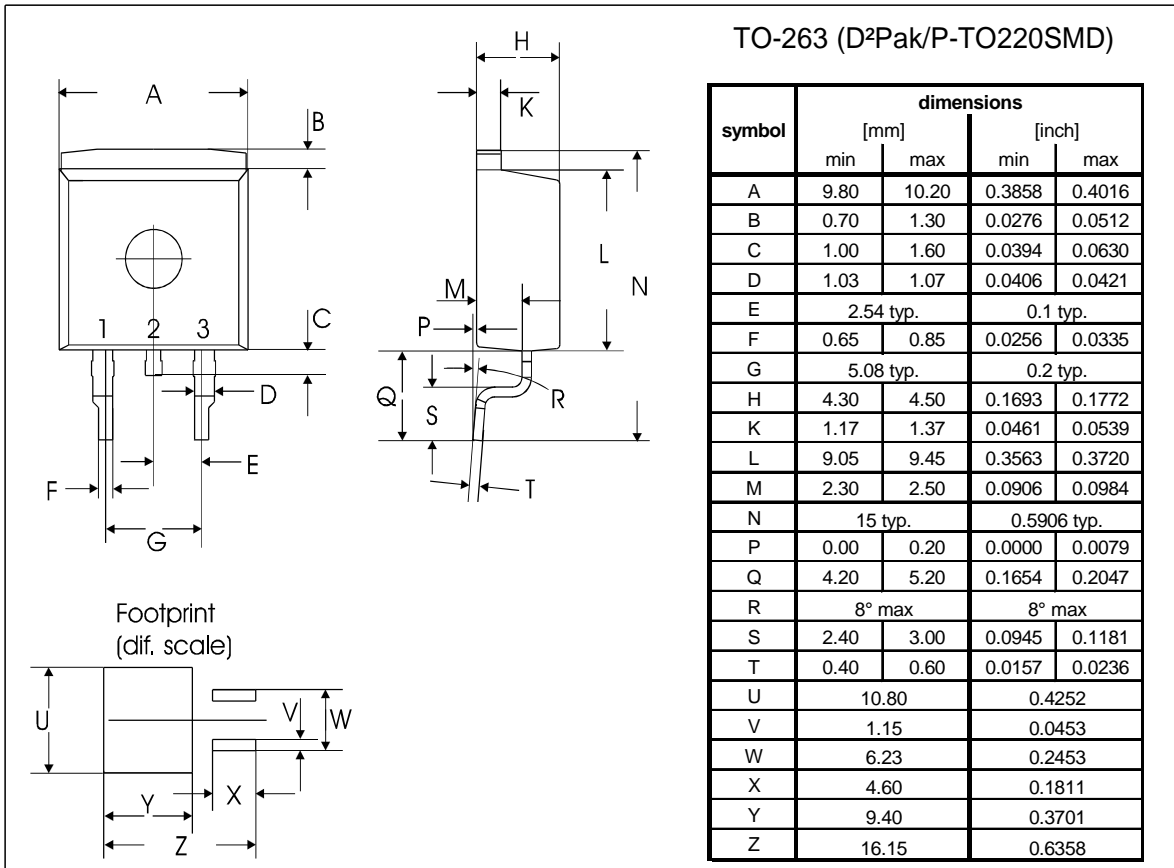
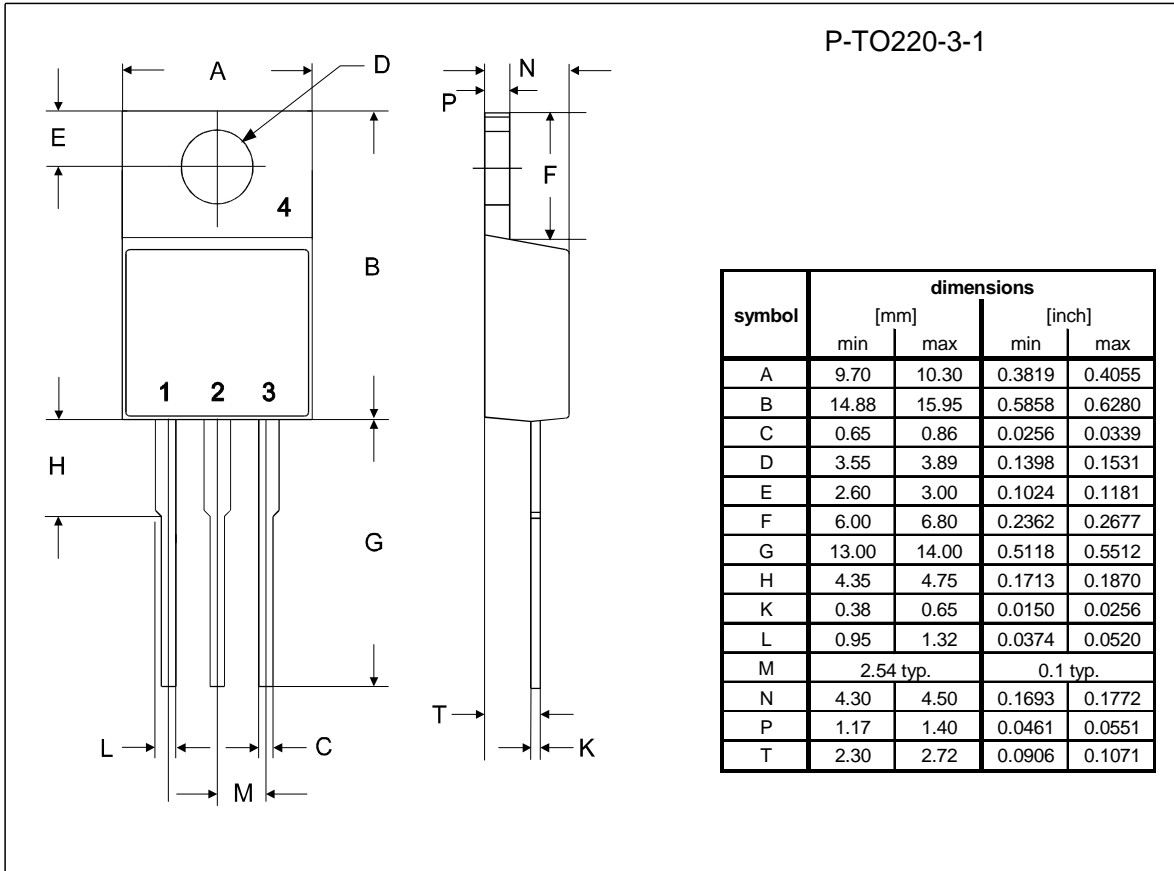


Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = 7.3 \text{ A pulsed}$





Published by
Infineon Technologies AG,
Bereichs Kommunikation
St.-Martin-Strasse 53,
D-81541 München
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